

Triacs

Silicon Bidirectional Triode Thyristors

... designed primarily for industrial and military applications for the control of ac loads in applications such as power supplies, heating controls, motor controls, welding equipment and power switching systems; or wherever full-wave, silicon gate controlled solid-state devices are needed.

- Glass Passivated Junctions and Center Gate Fire
- Press Fit Stud — T6400
Stud — T6410
Isolated Stud — T6420
- Gate Triggering Guaranteed in All 4 Quadrants

**T6400
T6410
T6420
Series**

**TRIACs
40 AMPERES RMS
200 thru 800 VOLTS**



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage, Note 1 ($T_J = -65$ to $+110^\circ\text{C}$) Gate Open T6400B, T6410B, T6420B T6400D, T6410D, T6420D T6400M, T6410M, T6420M T6400N, T6410N, T6420N	VDRM	200 400 600 800	Volts
On-State Current RMS (Conduction Angle = 360°) T_C (Pressfit) = 70°C T_C (Stud) = 65°C	$I_T(\text{RMS})$	40	Amps
Peak Surge Current (Non-Repetitive) (One Full Cycle, 60 Hz)	I_{TSM}	300	Amps
Circuit Fusing ($T_J = -65$ to $+110^\circ\text{C}$, $t = 1.25$ to 10 ms)	I^2t	450	A^2s
Peak Gate Power (Pulse Width = $10 \mu\text{s}$)	PGM	40	Watts
Average Gate Power	PG(AV)	0.75	Watt
Peak Gate Current (Pulse Width = $1 \mu\text{s}$)	I_{GTM}	12	Amps
Operating Temperature Range	T_C	-65 to $+110$	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to $+150$	$^\circ\text{C}$
Stud Torque	—	30	in. lb.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case Pressfit Stud Isolated Stud	$R_{\theta\text{JC}}$	0.8 0.9 1	$^\circ\text{C/W}$

Note 1. Ratings apply for open gate conditions. Thyristor devices shall not be tested with a constant current source for blocking capability such that the voltage applied exceeds the rated blocking voltage.



**CASE 263-04
STYLE 2
T6410
STUD**



**CASE 310-02
STYLE 2
T6400
PRESS FIT**



**CASE 311-02
STYLE 2
T6420
ISOLATED STUD**

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Forward or Reverse Blocking Current (Rated V_{DRM} or V_{RRM} , gate open) $T_J = 25^\circ\text{C}$ $T_J = 110^\circ\text{C}$	I_{DRM} , I_{RRM}	—	—	10 4	μA mA
Maximum On-State Voltage (Either Direction) ($I_T = 100$ A Peak)	V_{TM}	—	1.5	2	Volts
Gate Trigger Current (Continuous dc), Note 1 ($V_D = 12$ Vdc, $R_L = 30$ Ohms)	I_{GT}	—	15	50	mA
$V_{MT2(+), V_G(+)}$	—	30	80		
$V_{MT2(+), V_G(-)}$	—	20	50		
$V_{MT2(-), V_G(-)}$	—	40	80		
$V_{MT2(-), V_G(+)}$	—	—	125		
$V_{MT2(+), V_G(+), V_{MT2(-), V_G(-)}, T_C = -65^\circ\text{C}$ $V_{MT2(+), V_G(-), V_{MT2(-), V_G(+)}, T_C = -65^\circ\text{C}$	—	—	240		
Gate Trigger Voltage (Continuous dc) ($V_D = 12$ Vdc, $R_L = 30$ Ohms, $T_C = 25^\circ\text{C}$ $T_C = -65^\circ\text{C}$) ($V_D = \text{Rated } V_{DRM}$, $R_L = 125$ Ohms, $T_C = 110^\circ\text{C}$)	V_{GT}	— — 0.2	1.35 — —	2.5 3.4 —	Volts
Holding Current (Either Direction) ($V_D = 12$ Vdc, Gate Open) (Initiating Current = 500 mA) $T_C = 25^\circ\text{C}$ $T_C = -65^\circ\text{C}$	I_{HO}	— —	25 —	60 100	mA
Gate Controlled Turn-On Time (Rated V_{DRM} , $I_T = 60$ A, $I_{GT} = 200$ mA, Rise Time = 0.1 μs)	t_{gt}	—	1.7	3	μs
Critical Rate of Rise of Commutation Voltage, On-State Conditions ($di/dt = 22$ A/ms, Gate Unenergized, $V_D = \text{Rated } V_{DROM}$, $I_T(\text{RMS}) = 40$ A, T_C (Pressfit) = 70°C , T_C (Stud) = 65°C)	$dv/dt(c)$	—	5	—	V/ μs

Note 1. All voltage polarities referenced to main terminal 1.

FIGURE 1 – ON-STATE POWER DISSIPATION

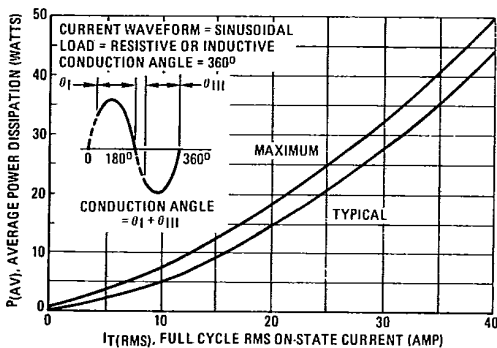


FIGURE 2 – RMS CURRENT DERATING

